

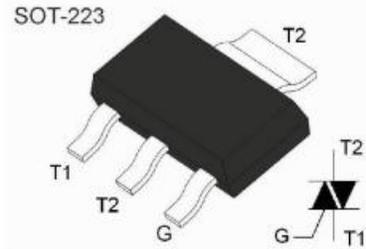
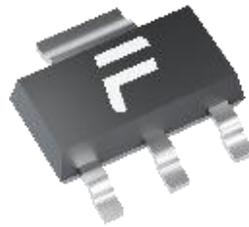
SOT-223 TRIAC 双向可控硅

■ Features 特点

Bidirectional switching and phase control 双向开关和相位控制
Glass passivated Process 玻璃钝化工艺

■ Applications 应用

Motor Control 马达控制
Industrial Lighting 工业照明
Heating Switching 加热开关



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Value 额定值	Unit 单位
Peak Repetitive Off-State Voltage 峰值可重复断态耐压	V_{DRM}, V_{RRM}	600 800	V
On-State RMS Current 通态均方根电流	$I_{T(RMS)}$	1	A
Peak Non-Repetitive Surge Current @25°C 峰值不可重复浪涌电流	I_{TSM}	t=20ms 10 t=16.7ms 11	A
Circuit Fusing Considerations(t=10ms) 电路保险指数	I^2t	0.5	A ² s
Peak Gate Current-Forward (Pulse Width ≤1 us) 正向门极峰值电流	I_{GM}	2	A
Peak Gate Voltage-Reverse (Pulse Width ≤ 1 μs) 反向门极峰值电压	V_{GRM}	5	V
Forward Peak Gate Power (Pulse Width ≤ 1 μs) 正向门极峰值功率	P_{GM}	5	W
Forward Average Gate Power (t=8.3ms) 正向门极平均功率	$P_{G(AV)}$	0.5	W
Critical rate of rise of on-state current 通态电流上升率 $I_{TM} = 6 A; I_G = 0.2 A;$ $dI_G/dt = 0.2 A/s$	dI/dt	T2+G+ 50 T2+G- 50 T2-G- 50 T2-G+ 10	A/μs
Thermal Resistance J-C 结到管壳热阻	$R_{θJC}$	15	°C/W

■ **Electrical Characteristics 电特性**

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic Parameters 特性参数	Symbol 符号	Min 最小值	Max 最大值				Unit 单位	Condition 条件		
			-B	-C	-D	-E				
Peak Forward Blocking Current 峰值正向漏电流	I_{DRM}	$T_c=25^{\circ}\text{C}$ $T_c=125^{\circ}\text{C}$	5 500				μA	$V_D=V_{\text{DRM}}$		
Peak Forward On-State Voltage 峰值正向通态电压	V_{TM}		1.5				V	$I_{\text{TM}}=2\text{A}$		
Gate Trigger Current 触发电流	I_{GT}	T2+G+ T2+G- T2-G- T2-G+	50 50 50 100	25 25 25 50	5 5 5 10	10 10 10 25	mA	$V_D=12\text{V}$ $I_T=0.1\text{A}$		
Gate Trigger Voltage 触发电压	V_{GT}		1.5						V	$V_D=12\text{V}$ $I_T=0.1\text{A}$
Holding Current 维持电流(T/D)	I_{H}		50	25	10	15			mA	$V_D=12\text{V}$ $I_{\text{GT}}=0.1\text{A}$
Latch Current 擎住电流(T/D)	I_{L}	T2+G+ T2+G- T2-G- T2-G+	50 50 50 100	40 40 40 80	10 10 10 10	15 15 15 15				
Gate Nun Trigger Voltage 门极不触发电压	V_{GD}	0.25					V	$V_D=V_{\text{DRM}}$		
Characteristic Parameters 特性参数	Symbol 符号	Type 典型值	Min 最小值				Unit 单位	Condition 条件		
			-B	-C	-D	-E				
Off-state Voltage Change 断态电压临界上升率(T/D)	dv/dt	250	400	200	10	20	$\text{V}/\mu\text{S}$	$V_D=2/3V_{\text{DRM}}$		
Off-state Voltage Change Com 断态电压累积上升率(T/D)	$dv/dt(\text{C})$	50	$I_T(\text{RMS}) = 1\text{A};$ $dI_{\text{com}}/dt = 1.8\text{A/ms}$				V/mS	$V_D=2/3V_{\text{DRM}}$		
Gate controlled turn-on time 门极控制开通时间	t_{gt}	2	$I_G=0.1\text{A};$ $dI_G/dt = 5\text{A}/\mu\text{s}$				μS	$I_{\text{TM}}=1.5\text{A}$ $V_D=V_{\text{DRM}}$		

■ Typical Characteristic Curve 典型特性曲线

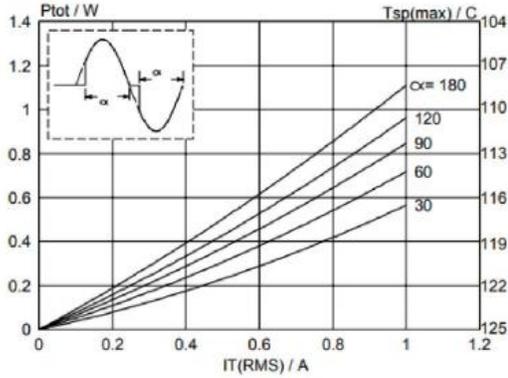


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

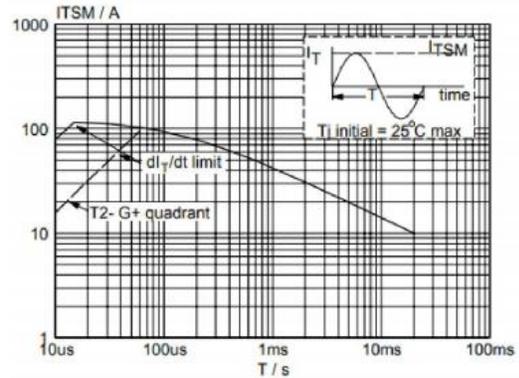


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20ms$.

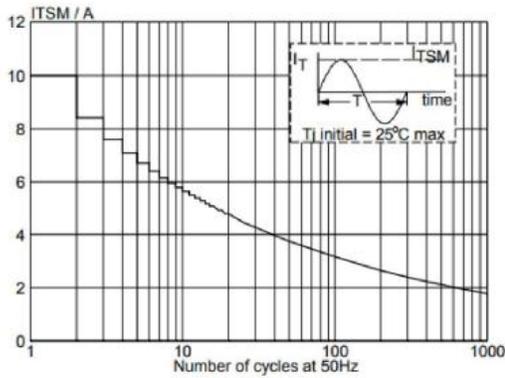


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50 Hz$.

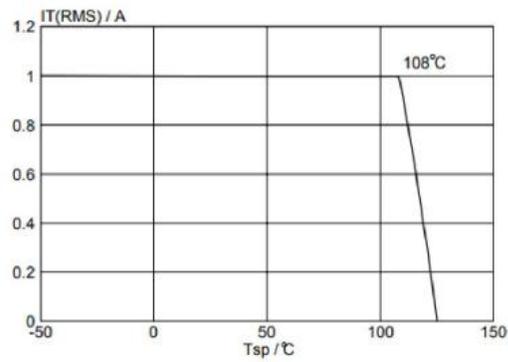


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus solder point temperature T_{sp} .

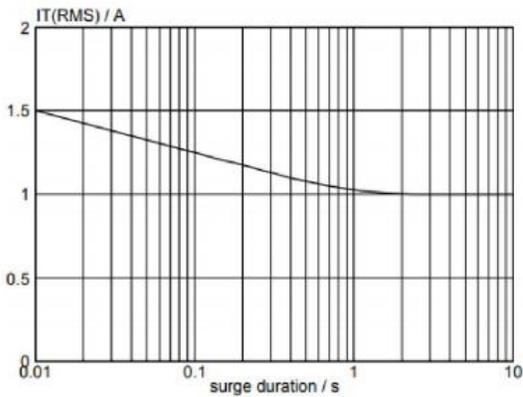


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents. $f = 50Hz$; $T_{cn} \leq 108^\circ C$.

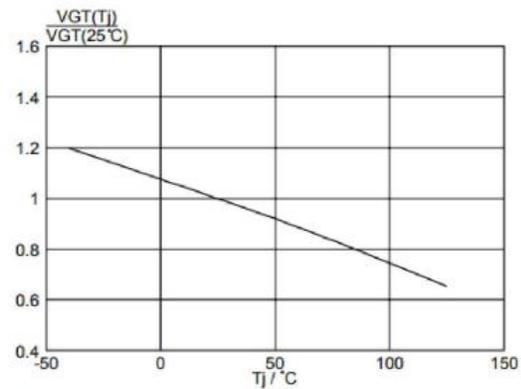


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^\circ C)$, versus junction temperature T_j .

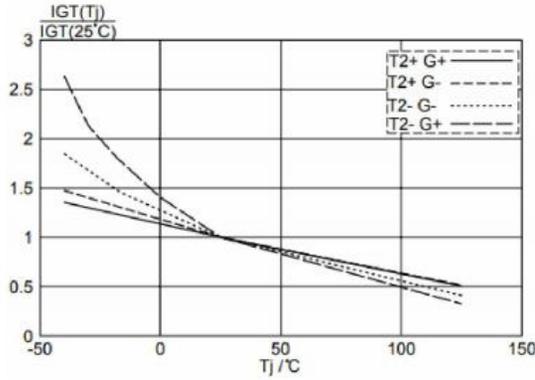


Fig.7. Normalised gate trigger current $I_{GT}(T_j) / I_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

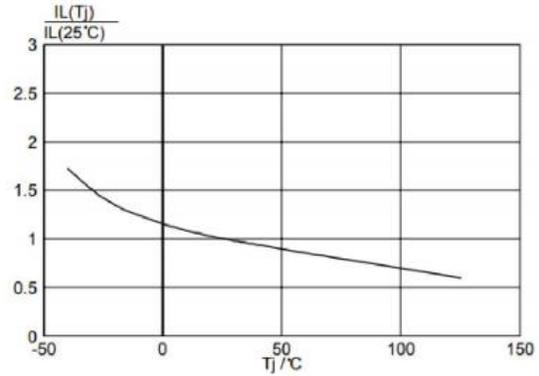


Fig.8. Normalised latching current $I_L(T_j) / I_L(25^\circ\text{C})$, versus junction temperature T_j .

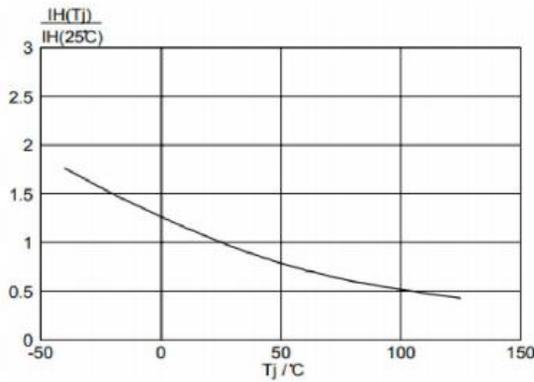


Fig.9. Normalised holding current $I_H(T_j) / I_H(25^\circ\text{C})$, versus junction temperature T_j .

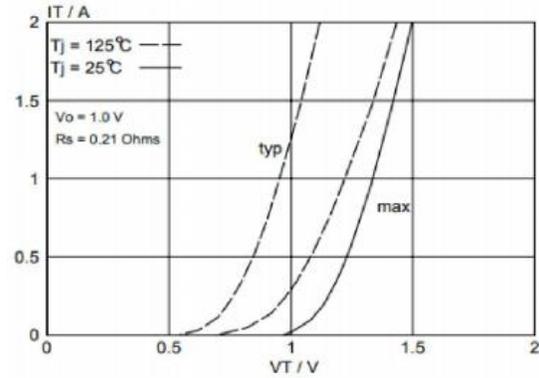


Fig.10. Typical and maximum on-state characteristic.

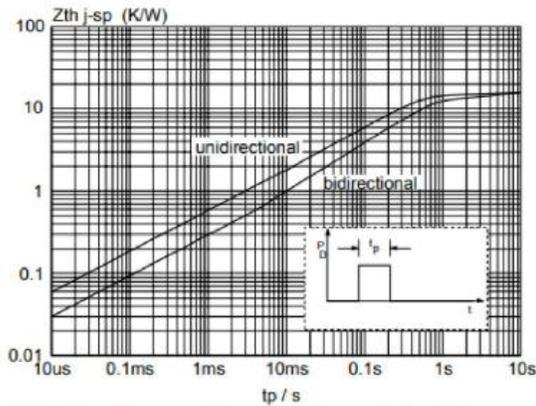


Fig.11. Transient thermal impedance $Z_{th\ j-sp}$, versus pulse width t_p .

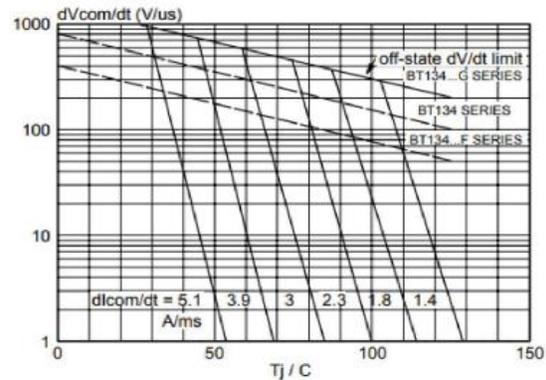


Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation dI_T/dt . The triac should commute when the dV/dt is below the value on the appropriate curve for pre-commutation dI_T/dt .

■ Dimension 外形封装尺寸

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	1.50	1.80	0.059	0.071
A1	0.00	0.10	0.000	0.004
A2	1.50	1.70	0.059	0.067
b	0.65	0.75	0.026	0.030
c	0.20	0.30	0.008	0.012
D	6.40	6.60	0.252	0.260
D1	2.90	3.10	0.114	0.122
E	3.30	3.70	0.130	0.146
E1	6.85	7.15	0.270	0.281
e	2.20	2.40	0.087	0.094
e1	4.40	4.80	0.173	0.189
L	1.65	1.85	0.065	0.073
L1	0.90	1.15	0.035	0.045